Docket Number (Optional) **Application Number** 15977-3 10/646.502 (Use several sheets if necessary) Applicant(s) Sungho Jin Filing Date Group Art Unit 08/23/2003 2812 **U.S. PATENT DOCUMENTS** DOCUMENT NUMBER CLASS SUBCLASS REF DATE (MM-YYYY) NAME IF APPROPRIATE 05-2000 74.1 6,069,599 Py et al. 345 6,411,020 313 06-2002 Yaniv et al. 310 427 6,103,305 08-2000 Friedmann et al. 249.7 4,149,076 04-1979 Albert 378 98.6 6,545,425 04-2003 Victor 315 169.3 6,297,063 10-2001 Brown et al. 438 2 429 231.8 6,465,132 10-2002 Jin 6,538,367 03-2003 Choi et al. 313 309 5.566,704 05-2003 Choi et al. 257 314 6,664,727 12-2003 Nakamoto 313 495 01-2004 Lee et al. 427 249.1 6,673,392 6,741,019 05-2004 Filas et al. 313 355 5,982,095 11-1999 Jin et al. 313 582 OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Zhu et. al., "Large Current Density from Carbon Nanotube Field Emitters." Applied Physics Letters, Vol. 75, No. 6, pgs. 873-875 (1999) Betzig, E. et al., "Near-Field Optics: Microscopy, Spectroscopy, and Surface Modification Beyond the Diffraction Limit", Science, Vol. 257, pgs 189-195 (July 10, 1992) Cheng et al., "Bulk morphology and diameter distribution of single-walled carbon nanotubes synthesized by catalytic decomposition of hydrocarbons", Chem. Physics Letters, Vol. 289, pg. 602-610 (1998) Date Considered 9 Examiner Signature EXAMINER! Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through

citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-A820 (also form PTO-1449)

SHEET 1 OF 3

					Docket Number (Optional) 15977-3	Application Number 10/646,502			
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